

DMTH6004SPS-13 Datasheet



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DiGi Electronics Part Number DMTH6004SPS-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMTH6004SPS-13

Description MOSFET N-CH 60V 25A PWRDI5060

Detailed Description N-Channel 60 V 25A (Ta), 100A (Tc) 2.1W (Ta), 167W

(Tc) Surface Mount PowerDI5060-8



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMTH6004SPS-13	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	25A (Ta), 100A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	3.1mOhm @ 50A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 250μA	95.4 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	4556 pF @ 30 V
FET Feature:	Power Dissipation (Max):
	2.1W (Ta), 167W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
PowerDI5060-8	8-PowerTDFN
Base Product Number:	
DMTH6004	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 9)	
60V	3.1 m Ω @ V _{GS} = 10 V	100A	

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power-management applications.

- DC motor controls
- Synchronous rectifications
- DC/DC converters

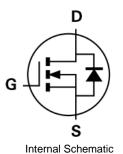
Features

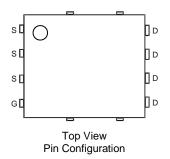
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable And Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_q Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (<u>DMTH6004SPSQ</u>)

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.097 grams (Approximate)







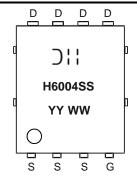
Ordering Information (Note 4)

Orderable Part Number	Dackers	Packing		
Orderable Part Number	Package	Qty.	Carrier	
DMTH6004SPS-13	PowerDI5060-8	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



The Manufacturer's Marking

H6004SS = Product Type Marking Code

YYWW = Date Code Marking

YY = Year (ex: 24 = 2024)

WW = Week (01 to 53)



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			V_{DSS}	60	V	
Gate-Source Voltage			Vgss	±20	V	
(Continuous Drain Current (Note 5)		$T_A = +25$ °C $T_A = +70$ °C	Δ	25 21	Α	
Continuous Drain Current (Notes 6 & 9) $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$		lo	100 100	Α		
Maximum Continuous Body Diode Forward Current (Notes 6 & 9)			Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		lом	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	400	Α
Avalanche Current, L = 0.2mH		las	45	Α		
Avalanche Energy, L = 0.2mH		Eas	200	mJ		

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	RθJA	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P _D	167	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	0.9	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

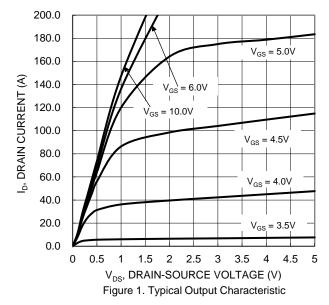
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

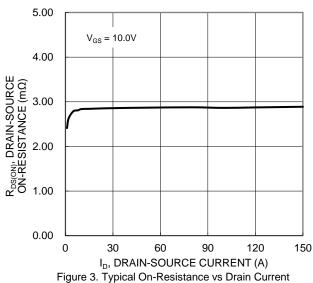
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60		_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_		1	μΑ	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss			±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2		4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)		2.5	3.1	mΩ	$V_{GS} = 10V, I_{D} = 50A$	
Diode Forward Voltage	VsD	_	0.9	1.2	V	V _G S = 0V, I _S = 20A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		4556			V _{DS} = 30V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	1383	_	pF		
Reverse Transfer Capacitance	Crss		105.2				
Gate Resistance	Rg	_	0.66	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg		95.4	_		V _{DD} = 30V, I _D = 90A, V _{GS} = 10V	
Gate-Source Charge	Qgs	_	21.6	_	nC		
Gate-Drain Charge	Qgd		20.4	_		VGS = 10V	
Turn-On Delay Time	td(on)	_	13.2	_			
Turn-On Rise Time	t _R	_	11.7	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 90A, R_{G} = 3.5\Omega$	
Turn-Off Delay Time	t _D (OFF)	_	31	_	ns		
Turn-Off Fall Time	tF	_	12	_			
Body Diode Reverse-Recovery Time	t _{RR}	_	50.5	_	ns	I= 500 di/dt 4000/us	
Body Diode Reverse-Recovery Charge	QRR	_	80.8	_	nC	I _F = 50A, di/dt = 100A/μs	

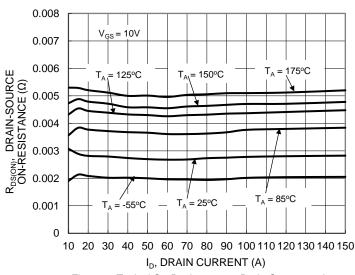
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.
- Short duration pulse test used to minimize sent neating 8. Guaranteed by design. Not subject to product testing.
- 9. Package limited.









and Gate Voltage

Figure 5. Typical On-Resistance vs Drain Current and Temperature

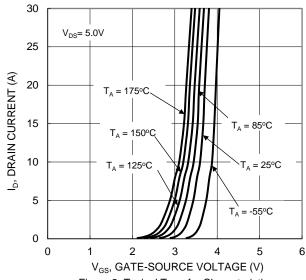


Figure 2. Typical Transfer Characteristic

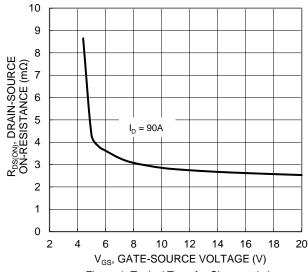


Figure 4. Typical Transfer Characteristic

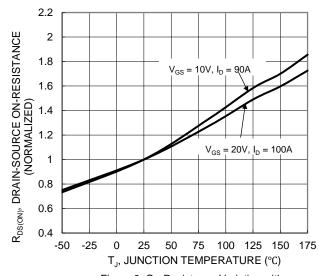


Figure 6. On-Resistance Variation with Temperature



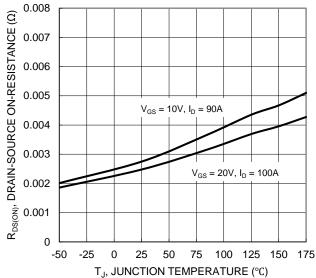
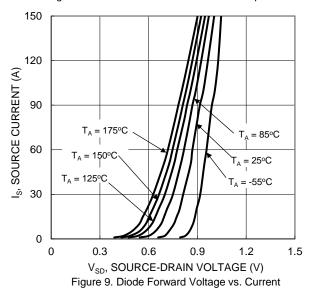
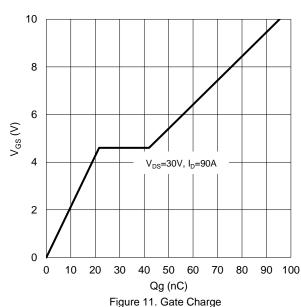


Figure 7. On-Resistance Variation with Temperature





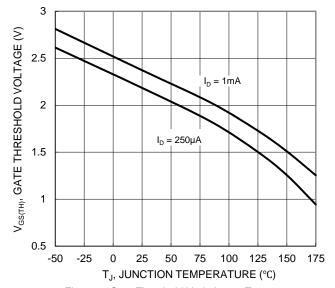


Figure 8. Gate Threshold Variation vs Temperature

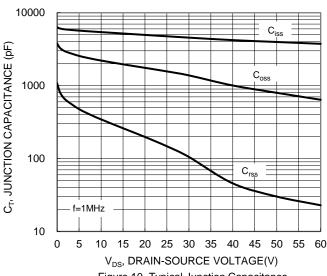
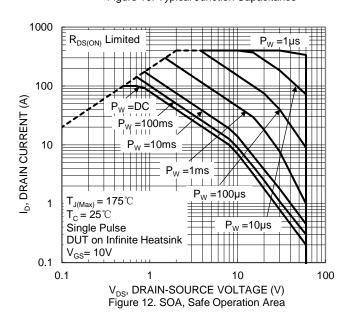


Figure 10. Typical Junction Capacitance





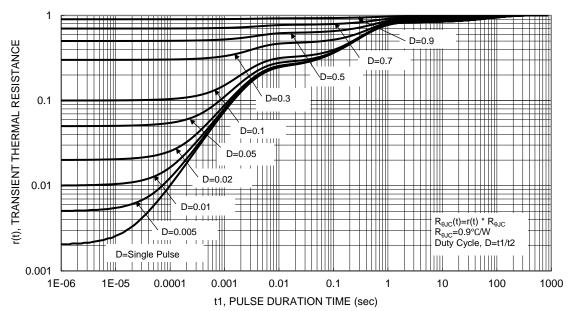


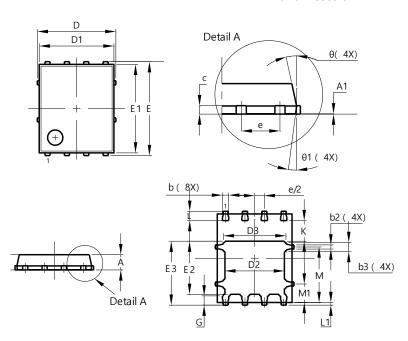
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

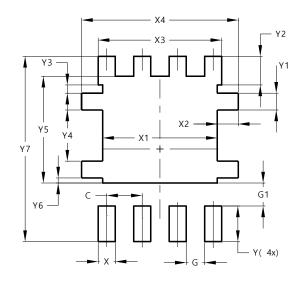


PowerDI5060-8						
D:						
			Тур			
Α	0.90	1.10	1.00			
A1	0.00	0.05	-			
b	0.33	0.51	0.41			
b2	0.200	0.350	0.273			
b3	0.40	0.80	0.60			
С	0.230	0.330	0.277			
D	ţ	5.15 BSC	;			
D1	4.70	5.10	4.90			
D2	3.70	4.10	3.90			
D3	3.90	4.30	4.10			
E	6.15 BSC					
E1	5.60	6.00	5.80			
E2	3.28	3.68	3.48			
E3	3.99	4.39	4.19			
е	1.27 BSC					
G	0.51	0.71	0.61			
K	0.51	_	_			
L	0.51	0.71	0.61			
L1	0.100	0.200	0.175			
М	3.235	4.035	3.635			
M1	1.00	1.40	1.21			
Θ	10°	12°	11°			
Θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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